

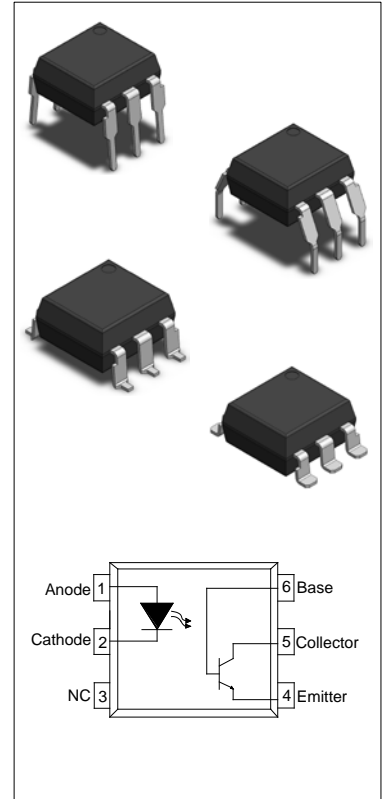


CNY17-X Series

Rev.A.1.0

DESCRIPTION:

The CNY17-X series combine an AlGaAs infrared emitting diode as the emitter which is optically coupled to a silicon planar phototransistor detector in a plastic DIP6 package with different lead forming options. The products are widely used in switch mode power supplies, programmable controllers, household appliances and office equipment.



MAIN FEATURES

- High isolation 5000 VRMS
- CTR flexibility available see order information
- DC input with transistor output
- Operating temperature range -55°C to 110°C
- REACH compliance
- Halogen free
- CQC approved
- VDE approved
- UL approved

ABSOLUTE MAXIMUM RATINGS (Temperature=25°C)

Parameter		Symbol	Value	Unit
Input	Forward current	I_F	60	mA
	Peak forward current	I_{FP}	1 ^①	A
	Reverse voltage	V_R	6	V
	Power dissipation	P_D	100	mW
Output	Collector-emitter Voltage	V_{CEO}	80	V
	Collector-base Voltage	V_{CBO}	80	V
	Emitter-collector Voltage	V_{ECO}	7	V
	Emitter- base Voltage	V_{EBO}	7	V
	Collector current	I_C	50	mA
	Output power dissipation	P_O	150	mW
Total Power Dissipation		P_{tot}	250	mW
Isolation Voltage		V_{iso}	5000 ^②	Vrms
Operating Temperature		T_{opr}	-55~+110	°C

Storage Temperature	T_{stg}	-55~+150	°C
Soldering Temperature	T_{sol}	260	°C

NOTE1: 100 μ s pulse, 100Hz frequency

NOTE2: AC for 1 minute, R.H.=40~60%

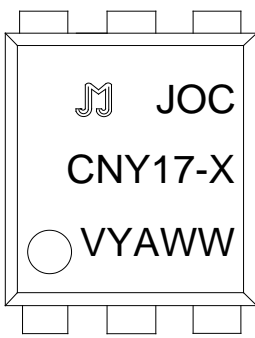
ELECTRICAL CHARACTERISTICS (Temperature=25°C)

Parameter		Symbol	Condition	Min.	Typ.	Max.	Unit
Input	Forward Voltage	V_F	$I_F=10mA$	-	1.27	1.4	V
			$I_F=20mA$	-	1.33	1.5	
	Reverse Current	I_R	$V_R=6V$	-	-	1	μA
	Input Capacitance	C_{in}	$V=0,$ $f=1MHz$	-	10	-	pF
Output	Collector-Emitter dark current	I_{CEO}	$V_{CE}=20V,$ $I_F=0$	-	-	100	nA
	Collector-Emitter breakdown voltage	BV_{CEO}	$I_C=0.1mA$ $I_F=0$	80	-	-	V
	Collector-Base breakdown voltage	BV_{CBO}	$I_C=0.1mA$ $I_F=0$	80	-	-	V
	Emitter-Collector breakdown voltage	BV_{ECO}	$I_E=0.1mA$ $I_F=0$	7	-	-	V
	Emitter-Base breakdown voltage	BV_{EBO}	$I_E=0.1mA$ $I_F=0$	7	-	-	V
Transfer Characteristics	DC Forward current gain	h_{FE}	$V_{CE}=5V,$ $I_C=0.5mA$	100	-	600	-
	Current transfer ratio	$CTR^{\text{①}}$	$I_F=10mA$ $V_{CE}=5V$	40	-	320	%
	Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_F=10mA$ $I_C=2.5mA$	-	-	0.3	V
	Isolation resistance	R_{IO}	DC500V 40~60%R.H.	10^{12}	10^{14}	-	Ω
	Floating Capacitance	C_{IO}	$V=0,$ $f=1MHz$	-	0.5	1	pF
	Cut-off Frequency	f_c	$V_{CE}=5V,$ $I_C=2mA$ $R_L=100\Omega,$ -3dB	-	80	-	kHz
	Rise Time	t_r	$V_{CC}=10V,$ $I_C=2mA$ $R_L=100\Omega$	-	3	10	μs
	Fall Time	t_f		-	4	10	μs
Response Time	t_{on}	-		5	15	μs	
	t_{off}	-		4	15	μs	

NOTE1 : Rank Table of Current Transfer Ratio (Temperature=25°C)

Grade Sign	Min. (%)	Max. (%)
1	40	80
2	63	125
3	100	200
4	160	320

ORDERING AND MARKING INFORMATION

MARKING INFORMATION			
		<p>JOC : Company Abbr. CNY17-X : Part Number & Rank VYAWW : LOT NO.</p>	
ORDERING INFORMATION			
CNY17-X(Y)(Z)-GV			
<p>CNY17 – Part Number X – Rank (X=1 to 4) Y – Lead Form Option (M/S/SL/None) Z – Tape and Reel Option (T1/T2) G – Material Option (G: Green, None: Non-Green) V – VDE Option (V or None)</p>			
Packing Quantity			
Option	Quantity	Quantity – Inner box	Quantity –Outer box
None/M	65 Units/Tube	32 Tubes/Inner box	10 Inner box/Outer box =20.8k Units
S(T1/T2)	1000 Units/Reel	3 Reels/Inner box	5 Inner box/Outer box =15k Units
SL(T1/T2)	1000 Units/Reel	3 Reels/Inner box	5 Inner box/Outer box =15k Units

Characteristics Curves

FIG.1: Forward Current vs. Ambient Temperature

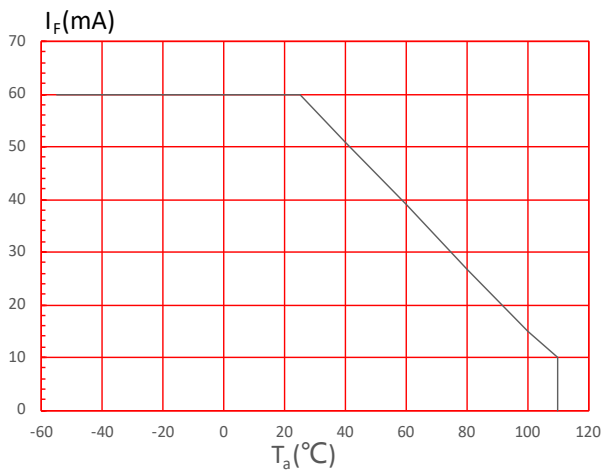


FIG.2: Collector Power Dissipation vs. Ambient Temperature

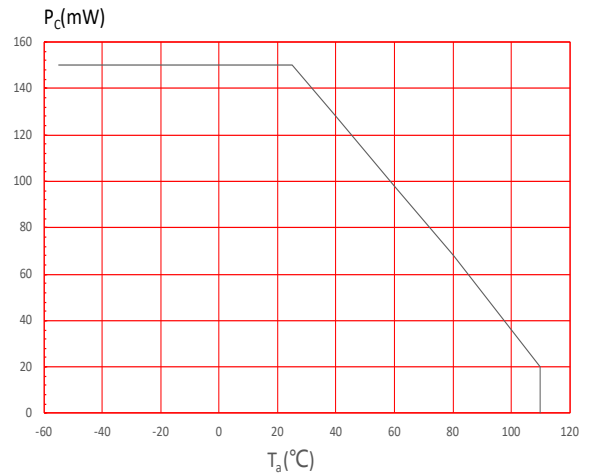


FIG.3: Forward Current vs. Forward Voltage

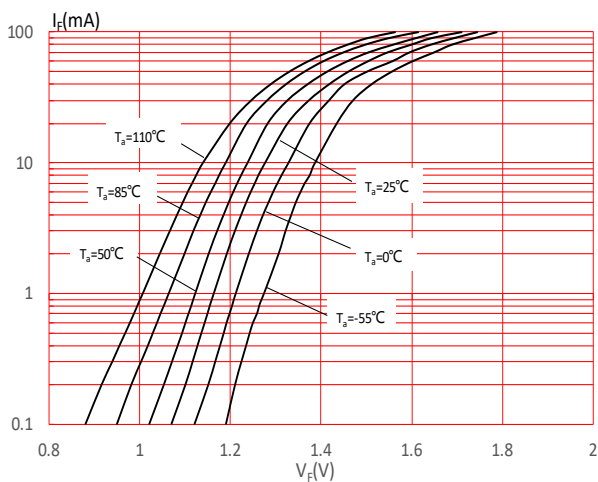


FIG.4: Normalized Collector Dark Current vs. Ambient Temperature

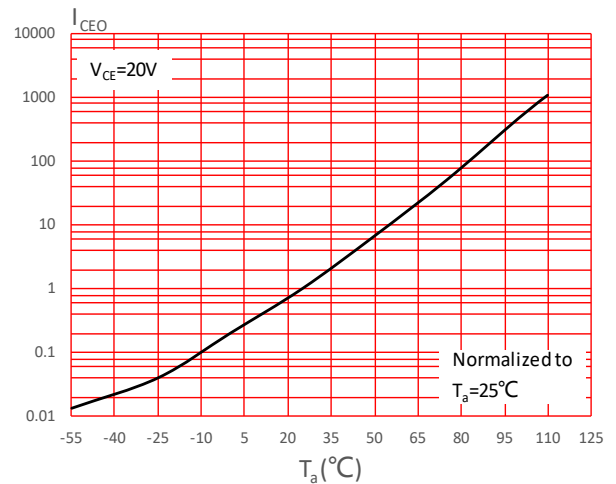


FIG.5: Collector Current vs. Collector-emitter Voltage

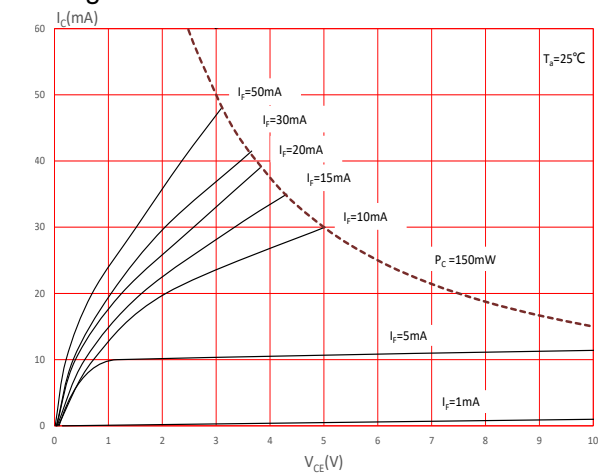


FIG.6: Normalized Current Transfer Ratio vs. Forward Current

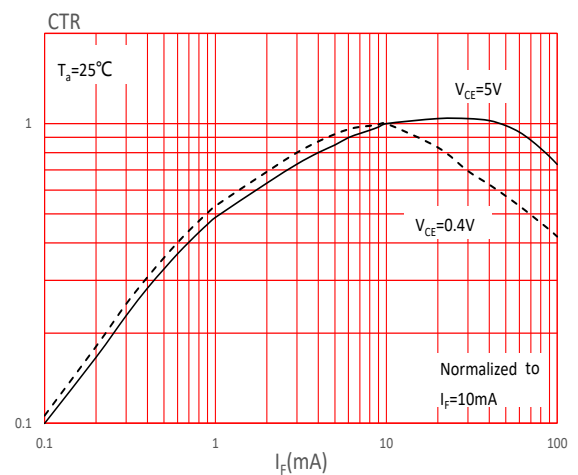


FIG.7: Normalized Current Transfer Ratio vs. Ambient Temperature

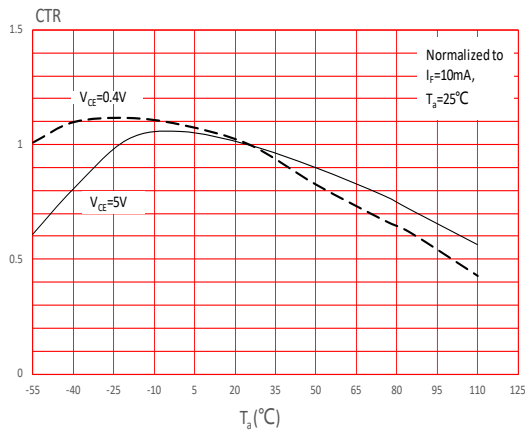


FIG.8: Normalized Collector-emitter Saturation Voltage vs. Ambient Temperature

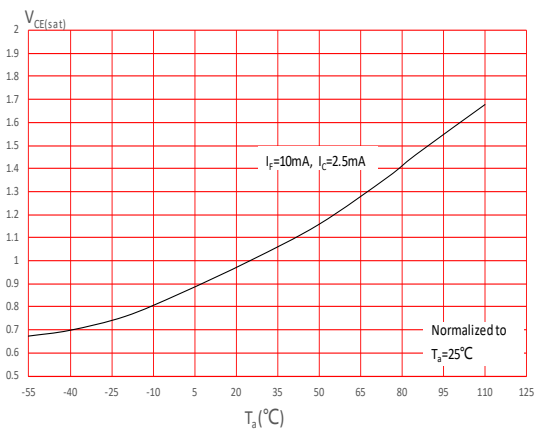


FIG.9: Current Transfer Ratio (Unsatrated) vs. Base-Emitter Resistance

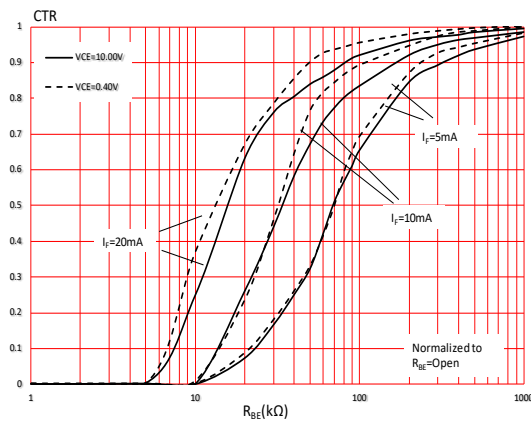


FIG.10: Response Time vs. Load Resistance

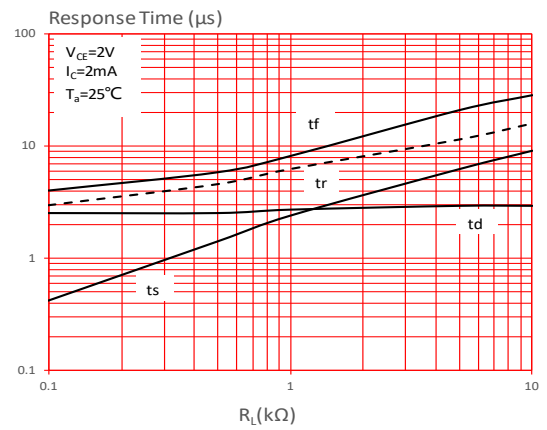


FIG.11: Frequency Response

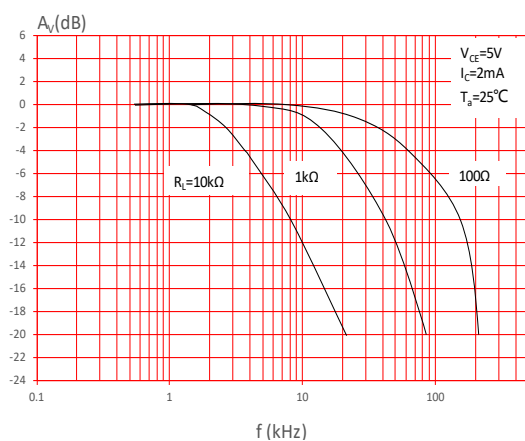
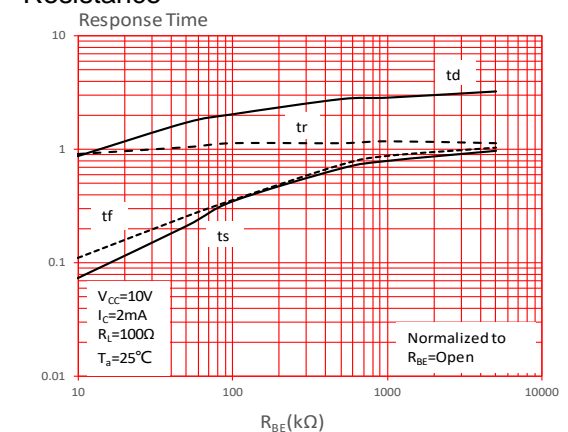


FIG.12: Response Time vs. Base-Emitter Resistance



Test Circuits

FIG.13: Test Circuits of Response Time

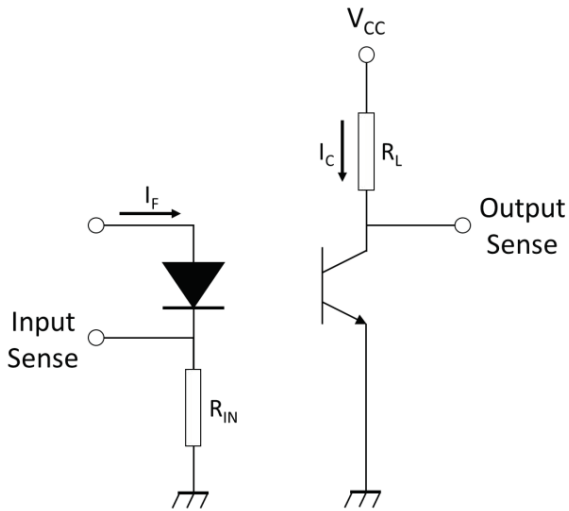


FIG.14: Curves of Response Time

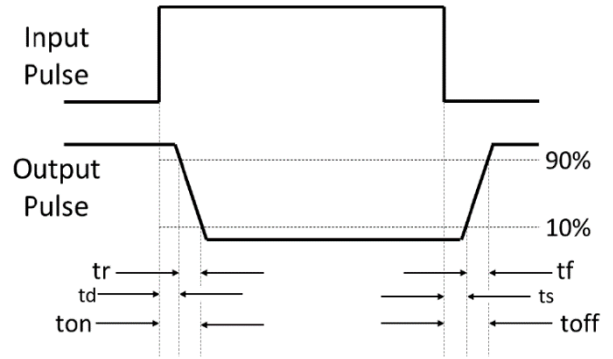
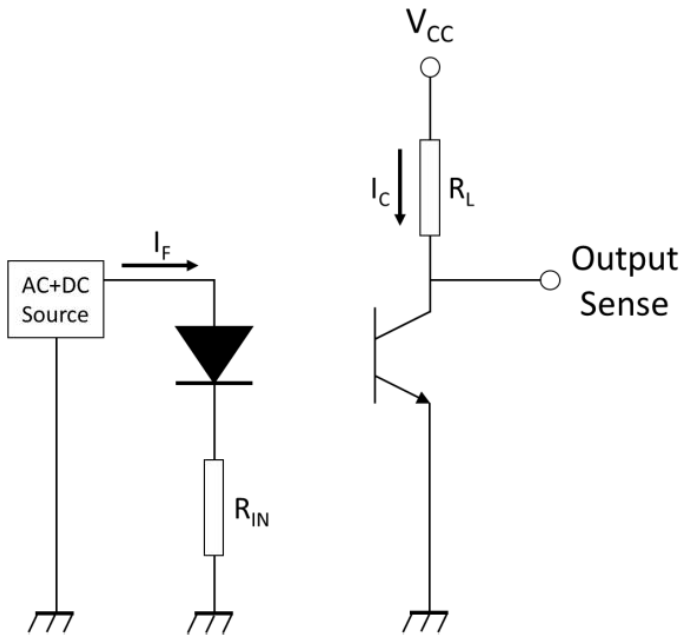
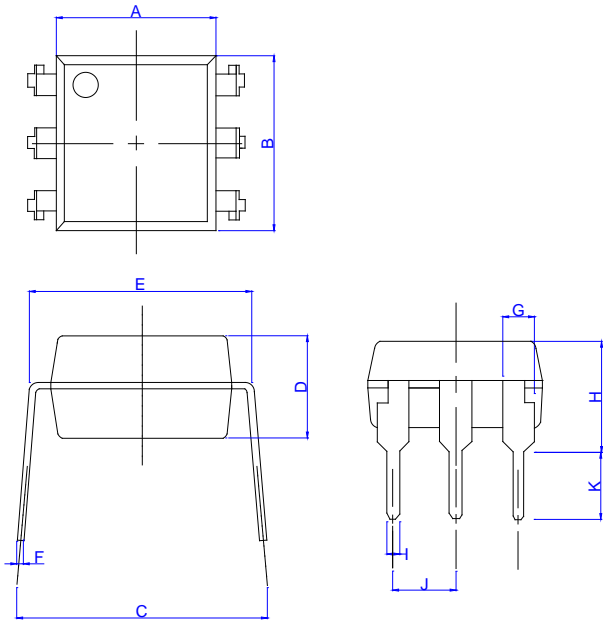


FIG.15: Test Circuits of Frequency Response



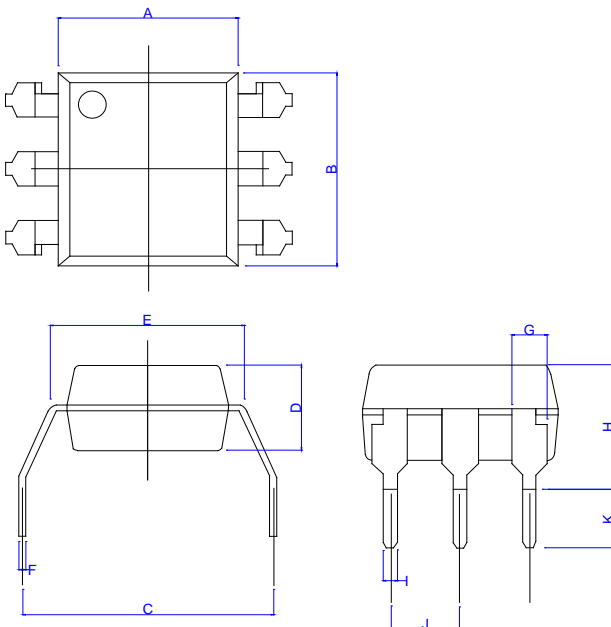
Package Dimension (Unit: mm)

Standard DIP Type:



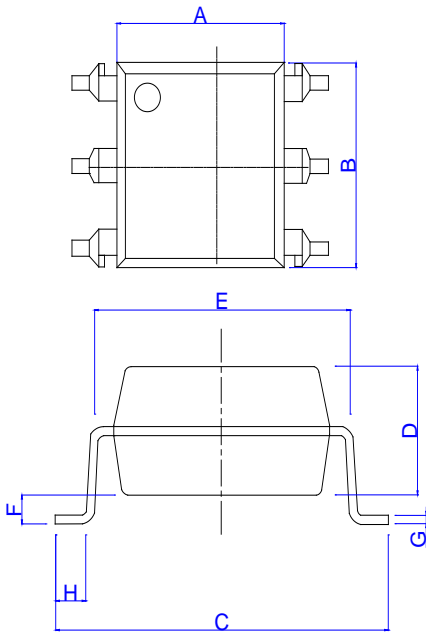
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	6.00		7.00	0.237		0.277
B	6.62		7.62	0.262		0.301
C	7.10		10.16	0.281		0.402
D	3.00		4.00	0.119		0.158
E	7.32		7.92	0.289		0.313
F	0.16		0.36	0.006		0.014
G	0.90		1.50	0.036		0.059
H	3.50		4.80	0.138		0.190
I	0.40		0.60	0.016		0.024
J	2.29		2.79	0.091		0.110
K	2.40		3.40	0.095		0.134

Option M Type:



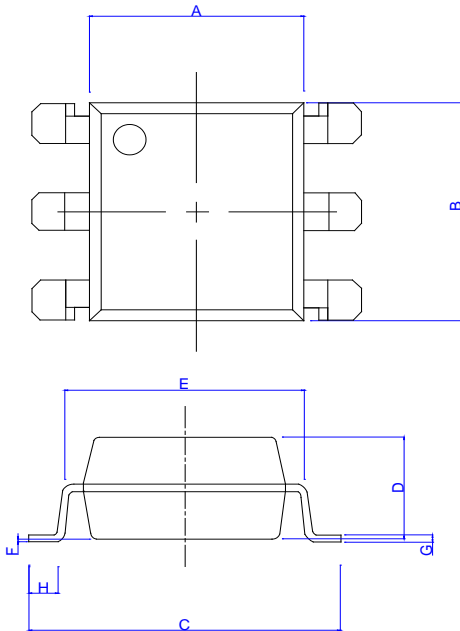
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	6.00		7.00	0.237		0.277
B	6.82		7.42	0.270		0.293
C	9.66		10.66	0.382		0.421
D	3.00		4.00	0.119		0.158
E	7.32		7.92	0.289		0.313
F	0.16		0.36	0.006		0.014
G	0.90		1.50	0.036		0.059
H	4.28		4.88	0.169		0.193
I	0.40		0.60	0.016		0.024
J	2.29		2.79	0.091		0.110
K	2.00		2.60	0.079		0.103

Option S Type:



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	6.30		6.70	0.249		0.265
B	6.92		7.32	0.274		0.289
C	9.85		10.45	0.389		0.413
D	3.30		3.70	0.130		0.146
E	7.32		7.92	0.289		0.313
F		0.80			0.032	
G		0.25			0.010	
H		0.80			0.032	
I	1.20		1.40	0.047		0.055
J	4.00		4.60	0.158		0.182
K		0.50			0.020	
L		2.54			0.100	

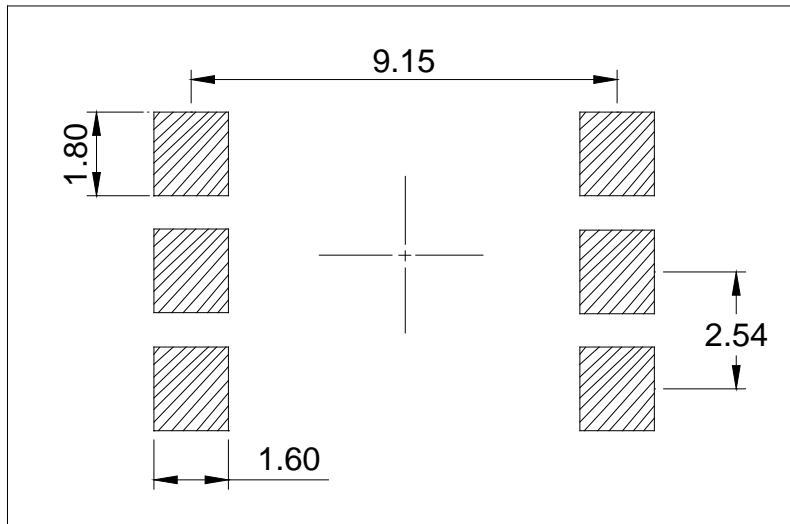
Option SL Type:



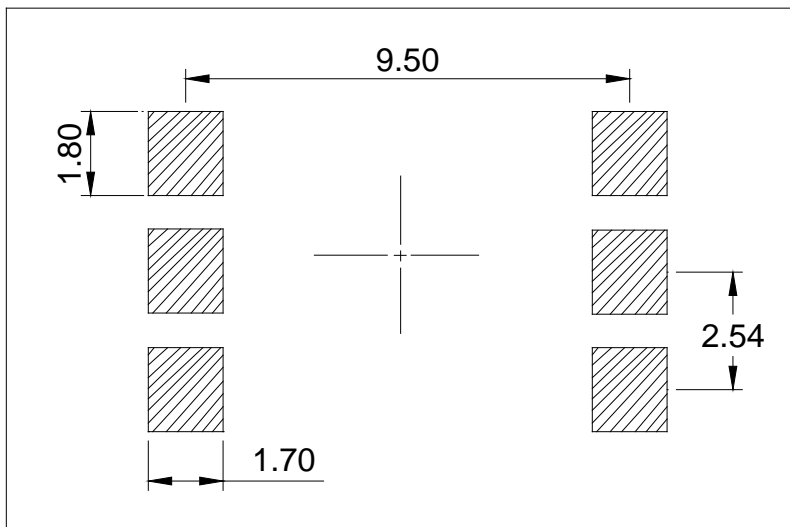
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	6.00		7.00	0.237		0.277
B	6.62		7.62	0.262		0.301
C	9.50		10.45	0.375		0.413
D	3.00		4.00	0.119		0.158
E	7.32		7.92	0.289		0.313
F	0.00		0.65	0.000		0.026
G	0.16		0.36	0.006		0.014
H	0.60		1.40	0.024		0.055
I	0.90		1.50	0.036		0.059
J	3.30		4.35	0.130		0.172
K	0.40		0.60	0.016		0.024
L	2.29		2.79	0.091		0.110

RECOMMENDED SOLDER MASK (Dimensions in mm unless otherwise stated)

Option S

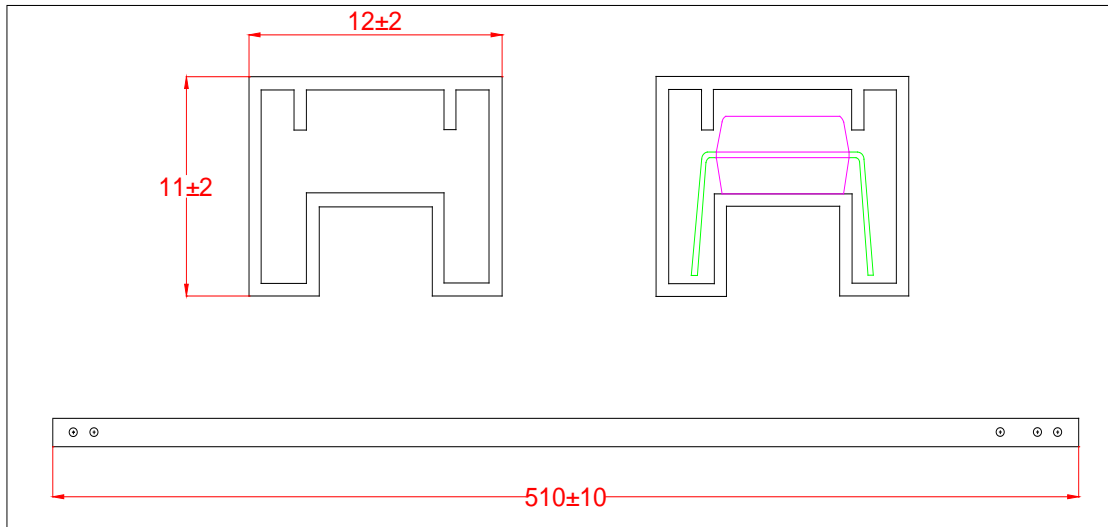


Option SL

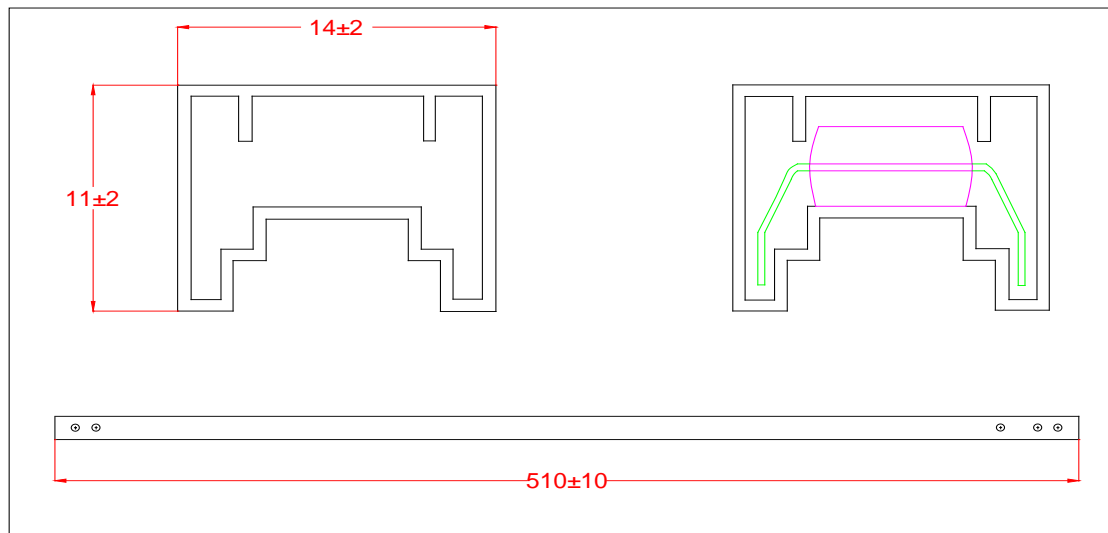


TUBE SPECIFICATIONS (Dimensions in mm unless otherwise stated)

Standard DIP

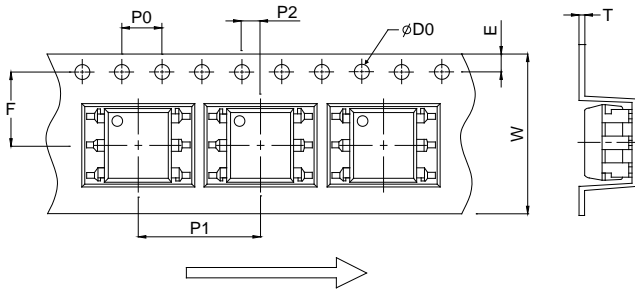


Option M

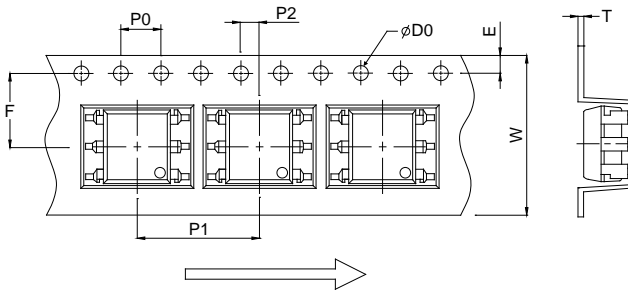


CARRIER TAPE SPECIFICATIONS (Dimensions in mm unless otherwise stated)

Option S(T1)

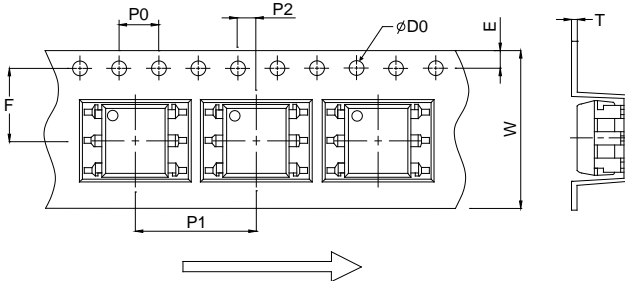


Option S(T2)

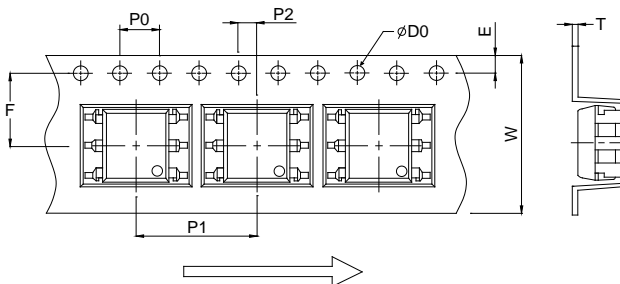


Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
D0		1.50	1.65		0.059	0.065
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	11.90	12.00	12.10	0.469	0.472	0.476
P2	1.90	2.00	2.10	0.075	0.079	0.083
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
T	0.25	0.35	0.45	0.010	0.014	0.018
W	15.70	16.00	16.30	0.618	0.630	0.642

Option SL(T1)

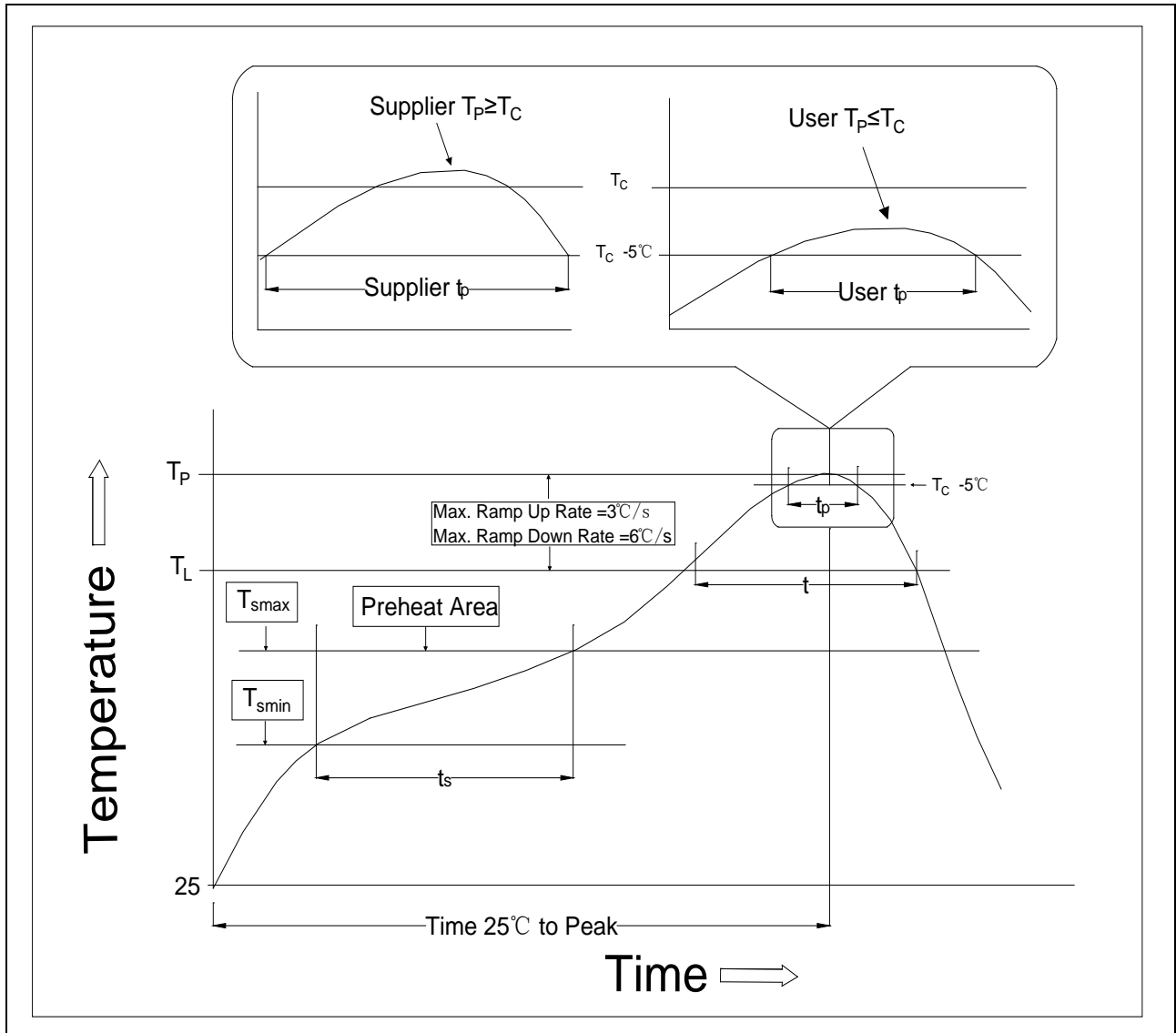


Option SL(T2)



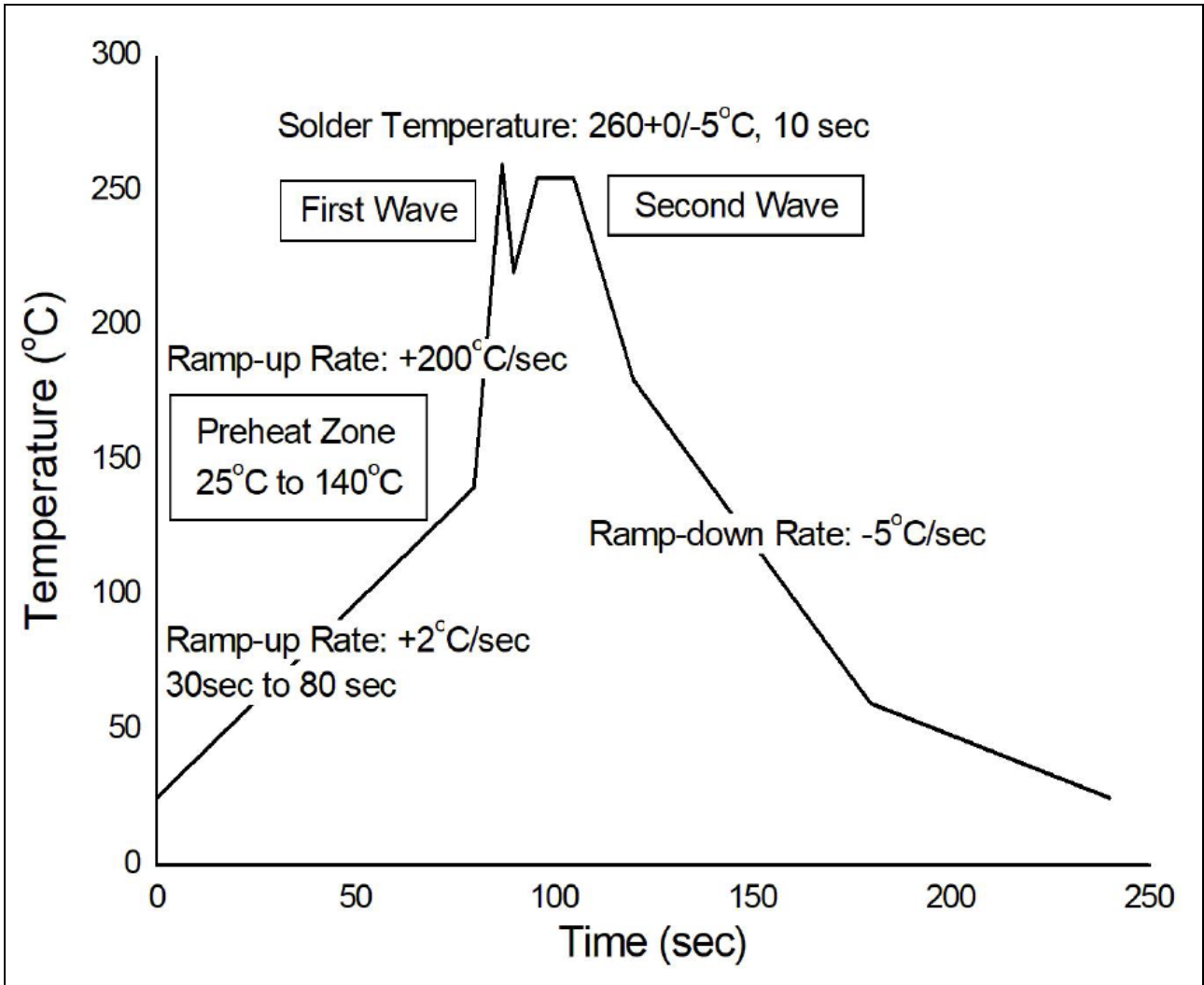
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
D0		1.50	1.60		0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	11.90	12.00	12.10	0.469	0.472	0.476
P2	1.90	2.00	2.10	0.075	0.079	0.083
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
T	0.35	0.40	0.45	0.014	0.016	0.018
W	15.70	16.00	16.30	0.618	0.630	0.642

REFLOW INFORMATION



Profile Feature	Sn-Pb Assembly Profile	Pb-Free Assembly Profile
Temperature Min. (T _{smin})	100	150°C
Temperature Max. (T _{smax})	150	200°C
Time (t _s) from (T _{smin} to T _{smax})	60-120 seconds	60-120 seconds
Ramp-up Rate (t _L to t _P)	3°C/second max.	3°C/second max.
Liquidus Temperature (T _L)	183°C	217°C
Time (t _L) Maintained Above (T _L)	60-150 seconds	60-150 seconds
Peak Body Package Temperature	235°C+0°C/-5°C	260°C+0°C/-5°C
Time (t _P) within 5°C of 260°C	20 seconds	30 seconds
Ramp-down Rate (T _P to T _L)	6°C/second max.	6°C/second max.
Time 25°C to Peak Temperature	6 minutes max.	8 minutes max.

WAVE SOLDERING




HAND SOLDERING BY SOLDERING IRON

Soldering Temperature	360±5°C
Soldering Time	3s max.

Information furnished in this document is believed to be accurate and reliable. However, Jiangsu JieJie Microelectronics Co., Ltd. assumes no responsibility for the consequences of use without consideration for such information nor use beyond it. Information mentioned in this document is subject to change without notice, apart from that when an agreement is signed, Jiangsu JieJie complies with the agreement.

Products and information provided in this document have no infringement of patents. Jiangsu JieJie assumes no responsibility for any infringement of other rights of third parties which may result from the use of such products and information. This document supersedes and replaces all information previously supplied.

 is a registered trademark of Jiangsu JieJie Microelectronics Co., Ltd.

Copyright © 2025 Jiangsu JieJie Microelectronics Co., Ltd. All rights reserved.